

Vishay Siliconix

N-Channel 40 V (D-S) 175 °C MOSFET

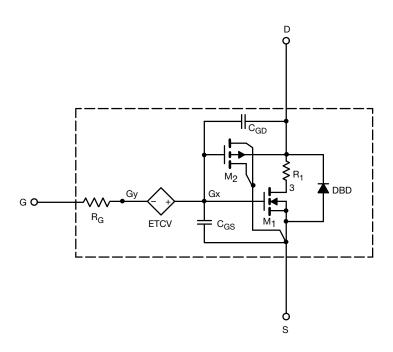
DESCRIPTION

The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the - 55 °C to + 125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage. A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched $C_{\rm gd}$ model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

SUBCIRCUIT MODEL SCHEMATIC

CHARACTERISTICS

- N-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the 55 °C to + 125 °C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics



Note

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

SPICE Device Model SQD50N04-4m5L

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SPECIFICATIONS T _J = 25 °C, unless otherwise noted					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.8	-	٧
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	0.0029	-	Ω
		$V_{GS} = 4.5 \text{ V}, I_D = 20 \text{ A}$	0.0035	-	
Forward Transconductancea	9 _{fs}	V _{DS} = 15 V, I _D = 15 A	37	57	S
Body Diode Voltage	V _{SD}	I _S = 30 A	1	0.90	V
Dynamic ^b					
Input Capacitance	C _{iss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz	4830	4880	pF
Output Capacitance	C _{oss}		727	560	
Reverse Transfer Capacitance	C _{rss}		307	250	
Total Gate Charge	Qg		85	85	
Gate-Source Charge	Q_{gs}	$V_{DS} = 20 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 50 \text{ A}$	14	14	nC
Gate-Drain Charge	Q _{gd}		14	14	

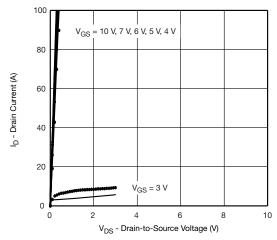
Notes

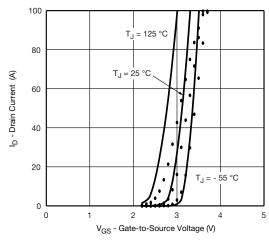
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

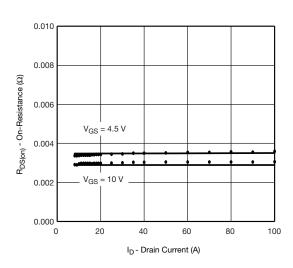


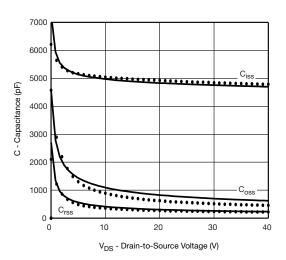
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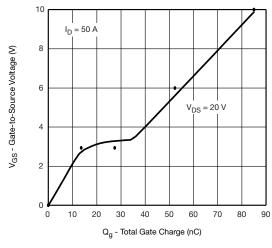
COMPARISON OF MODEL WITH MEASURED DATA $T_J = 25~{}^{\circ}\text{C}$, unless otherwise noted

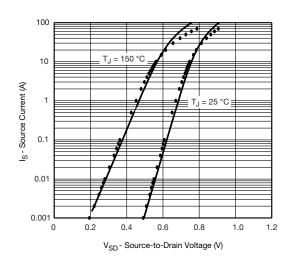












NoteDots and squares represent measured data.



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